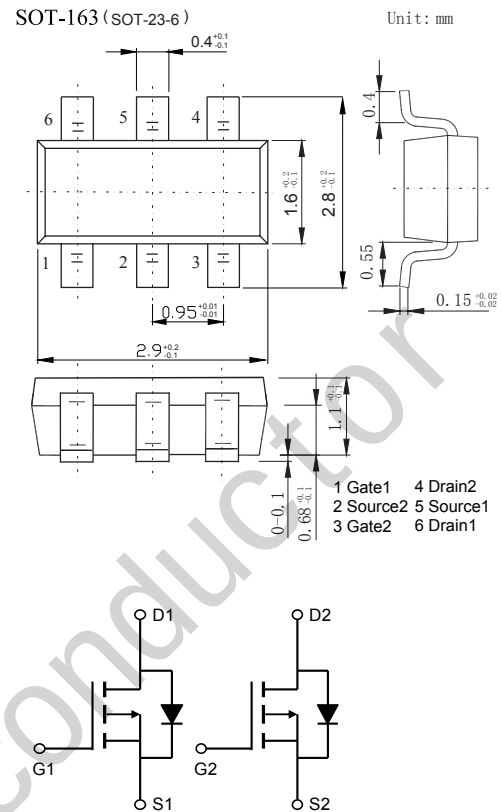


FEATURE

- ◆ **-20V/-3.0A, $R_{DS(ON)}=90m\Omega$ (typ.)@ $V_{GS}=4.5V$**
- ◆ **-20V/-2.2A, $R_{DS(ON)}=110m\Omega$ (typ.)@ $V_{GS}=2.5V$**
- ◆ Super high design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and Maximum DC current capability
- ◆ Full RoHS compliance
- ◆ SOT-23-6L package design

APPLICATIONS

- ◆ Power Management
- ◆ Portable Equipment
- ◆ DC/DC Converter
- ◆ Load Switch
- ◆ DSC
- ◆ LCD Display inverter



Absolute Maximum Ratings

$T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_b	Drain Current – Continuous – Pulsed	-3.0	A
		-8	
P_D	Power Dissipation for Single Operation	1.1	W
		0.96	
		0.8	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$
Thermal Characteristics			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	130	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	60	$^\circ\text{C/W}$

Electrical Characteristics
 $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _b = –250 μA	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _b = –250 μA, Referenced to 25°C		–11		mV/°C
I _{bSS}	Zero Gate Voltage Drain Current	V _{DS} = –16 V, V _{GS} = 0 V			–1	μA
I _{GSSF}	Gate–Body Leakage, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	V _{GS} = –12 V, V _{DS} = 0 V			–100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _b = –250 μA	–0.6	–1.0	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _b = –250 μA, Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = –4.5 V, I _b = –3.0 A V _{GS} = –2.5 V, I _b = –2.2 A V _{GS} = –4.5 V, I _b = –3.0 A, T _J = 125°C		90 110 127	105 153 155	mΩ
I _{b(on)}	On–State Drain Current	V _{GS} = –4.5 V, V _{DS} = –5 V	–6			A
g _{FS}	Forward Transconductance	V _{DS} = –5 V, I _b = –3.5 A		6		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = –10 V, V _{GS} = 0 V, f = 1.0 MHz		437		pF
C _{oss}	Output Capacitance			88		pF
C _{rss}	Reverse Transfer Capacitance			51		pF
Switching Characteristics						
t _{d(on)}	Turn–On Delay Time	V _{DD} = –10 V, I _b = –1 A, V _{GS} = –4.5 V, R _{GEN} = 6 Ω		9	18	ns
t _r	Turn–On Rise Time			12	22	ns
t _{d(off)}	Turn–Off Delay Time			10	20	ns
t _f	Turn–Off Fall Time			5	10	ns
Q _g	Total Gate Charge	V _{DS} = –10 V, I _b = –3.0 A, V _{GS} = –4.5 V		3.7	5.2	nC
Q _{gs}	Gate–Source Charge			0.65		nC
Q _{gd}	Gate–Drain Charge			1.3		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain–Source Diode Forward Current				–0.8	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = –0.8 A (Note 2)		0.77	–1.2	V

Typical Characteristics

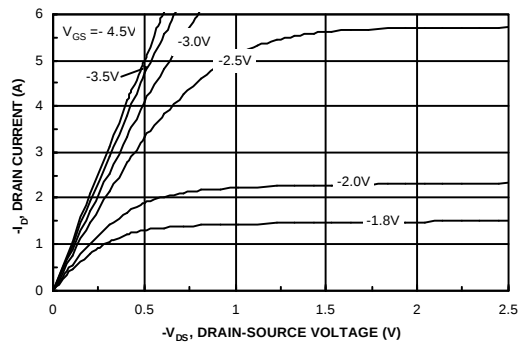


Figure 1. On-Region Characteristics.

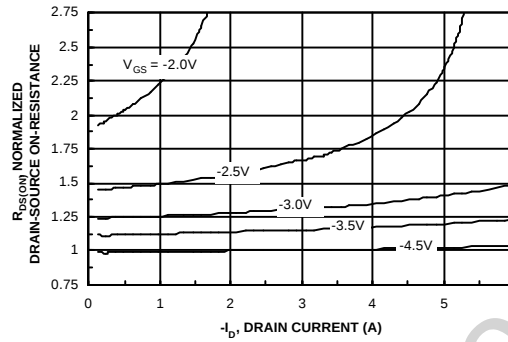


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

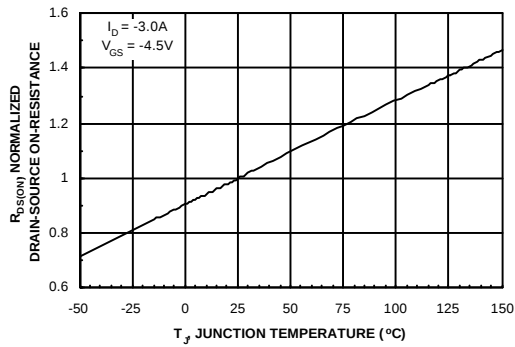


Figure 3. On-Resistance Variation with Temperature.

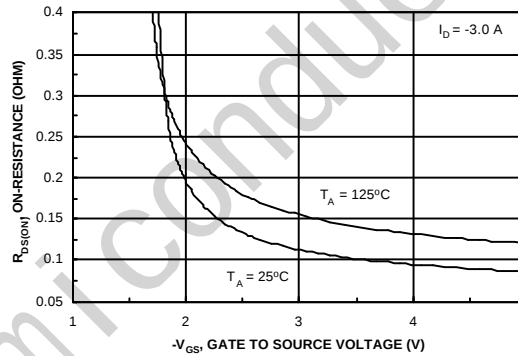


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

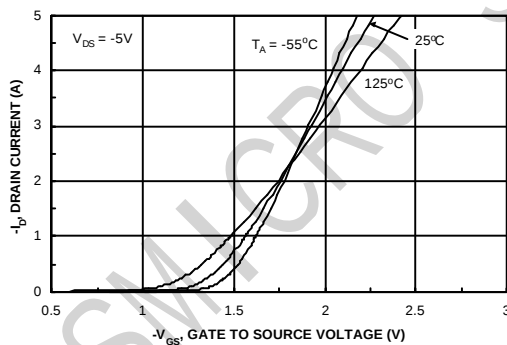


Figure 5. Transfer Characteristics.

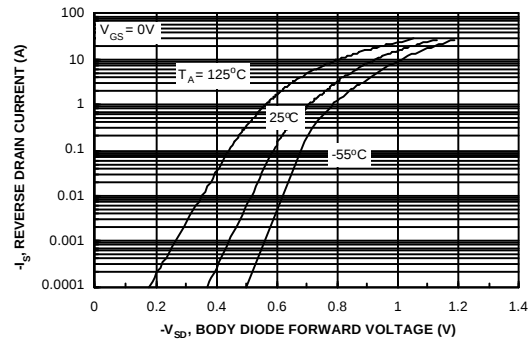


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

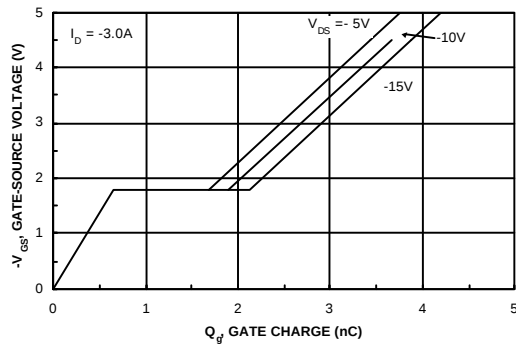


Figure 7. Gate Charge Characteristics.

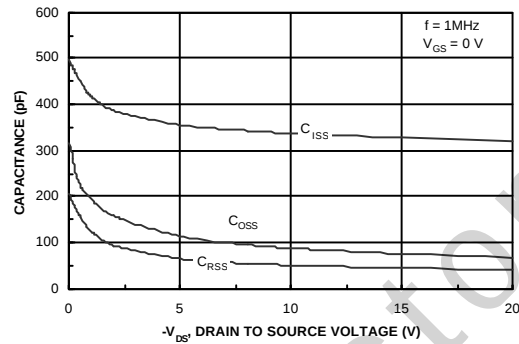


Figure 8. Capacitance Characteristics.

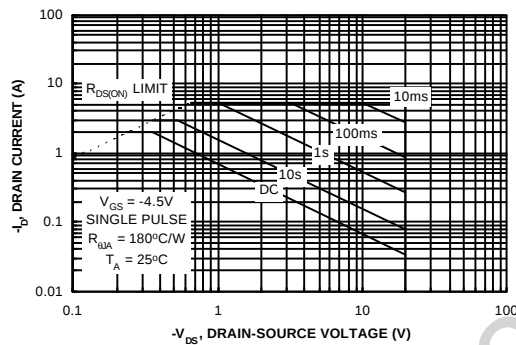


Figure 9. Maximum Safe Operating Area.

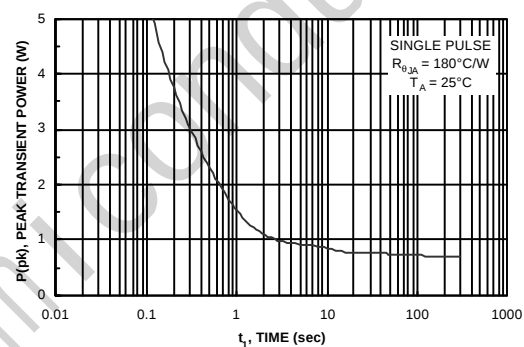


Figure 10. Single Pulse Maximum Power Dissipation.

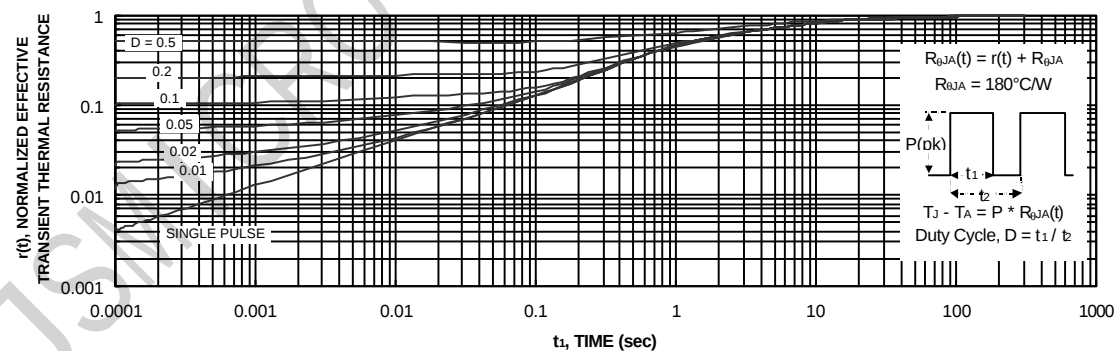
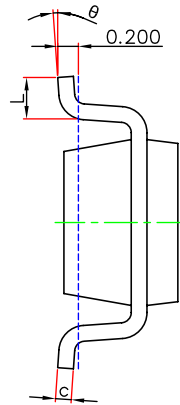
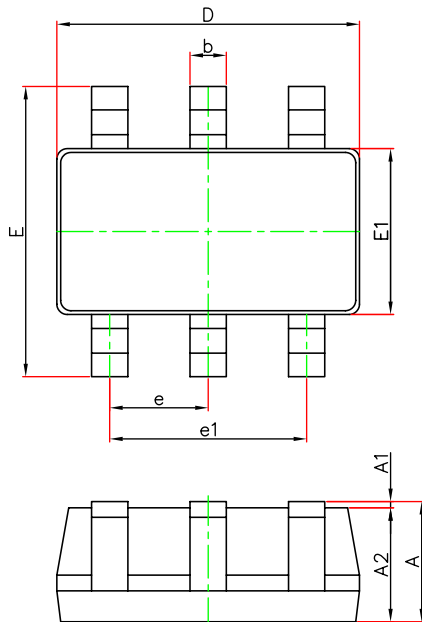


Figure 11. Transient Thermal Response Curve.

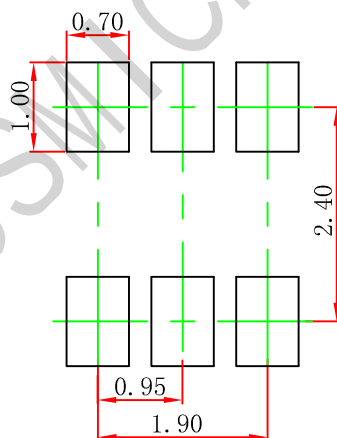
Thermal characterization performed using the conditions described in Note 1c.
 Transient thermal response will change depending on the circuit board design.

SOT-23-6L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

SOT-23-6L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.